2015 EE214A Design Project

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Abstract

Area Breakdown:

• PMOS Bias Gen: 25%

• NMOS Bias Gen: 25%

 \bullet Core circuit: 25%

• Resistors: 25%

1 Design Outline

Text of design outline

2 Design Schematic

Text of design schematic

3 Calculation of Key Design Parameters

Text of calculating key design parameters

4 Simulated Bode Plots

Text of bode plots

5 Simulated Transient Response

Text of transient response

6 Comments and Conclusion

Write your conclusion here.

7 Appendix I

Netlist here

8 Appendix II

Bonus problem here